


Trans RF MOSFET N-CH 110V 5-Pin NI-1230 T/R

Manufacturer:	NXP Semiconductor
Package/Case:	TO-59
Product Type:	Thyristors
RoHS:	RoHS Compliant/Lead free 
Lifecycle:	Obsolete



Images are for reference only

[Inquiry](#)

General Description

The MRF6VP11KHR6 and MRF6VP11KGSR5 are designed primarily for pulse wideband applications with frequencies up to 150 MHz. Device is unmatched and is suitable for use in industrial, medical and scientific applications.

Key Features

Typical Pulse Performance at 130 MHz: VDD = 50 Volts, IDQ = 150 mA, Pout = 1000 Watts Peak (200 W Avg.), Pulse Width = 100 µsec, Duty Cycle = 20% Power Gain: 26 dB Drain Efficiency: 71%

Capable of Handling 10:1 VSWR, @ 50 Vdc, 130 MHz, 1000 Watts Peak Power

Characterized with Series Equivalent Large-Signal Impedance Parameters

CW Operation Capability with Adequate Cooling

Qualified Up to a Maximum of 50 VDD Operation

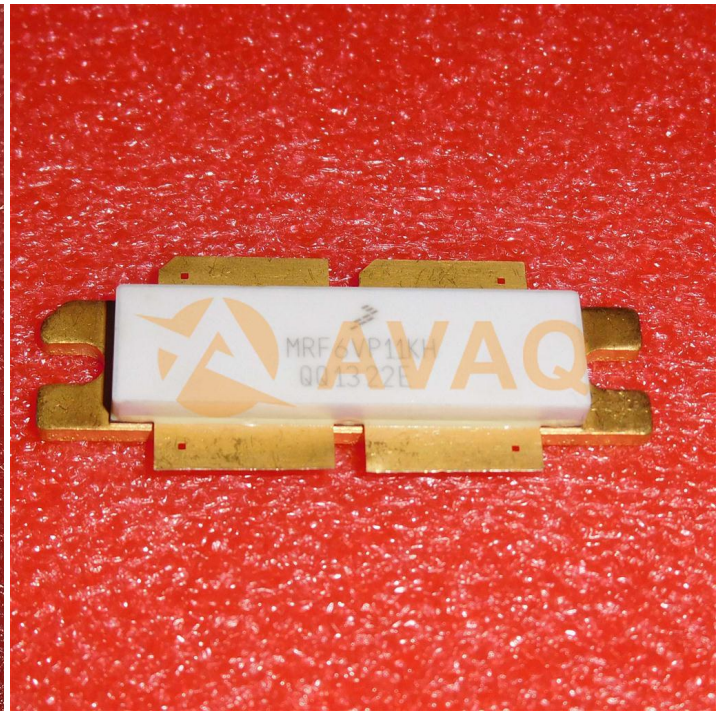
Integrated ESD Protection

Designed for Push-Pull Operation

Greater Negative Gate-Source Voltage Range for Improved Class C Operation

RoHS Compliant

In Tape and Reel. R6 Suffix = 150 Units, 56 mm Tape Width, 13 inch Reel. R5 Suffix = 50 Units, 56 mm Tape Width, 13 Inch Reel.



Recommended For You

MRF8S21100HSR3

NXP Semiconductor

SMD

MRFE6S20010NR1

NXP Semiconductor

SMD

MRFE6VP6300HR5

NXP Semiconductor

TO-59

MRFE6S9060NR1

NXP Semiconductor

SMD

MRFE6VP61K25HR6

NXP Semiconductor

TO-59

MRFE6VP3450HR5

NXP Semiconductor

TO-59

MRF6S18060NR1

NXP Semiconductor

TO-59

MRFE6P3300HR3

NXP Semiconductor

TO-59

MRF7S38040HSR3

NXP Semiconductor

SMD

MRF8S9102NR3

NXP Semiconductor

TO-59

MRFE6S9205HSR3

NXP Semiconductor

TO-59

MRF9135LR3

NXP Semiconductor

TO-59

MRFE6VP100HR5

NXP Semiconductor

TO-59

MRFX1K80NR5

NXP Semiconductor

SMD

MRFE6VS25NR1

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